

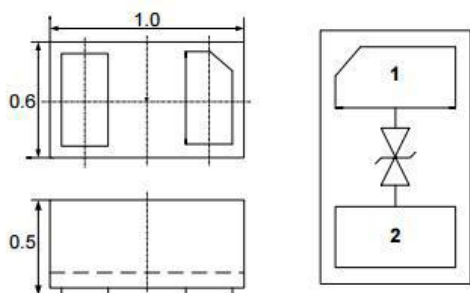
Description

SLESD3301 is a 1 line 3.3V bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The small size and high ESD surge protection make SLESD3301 an ideal choice to protect cell phone, digital cameras, audio players and many other portable applications.

Features

- Low junction capacitance(typical value: 0.25pF)
- Working voltage: 3.3V
- Low clamping voltage
- 2-pins leadless package
- RoHS Compliant

Dimensions & Symbol (Unit: mm Max)



Dimensions

Pin and Circuit Schematic

Mechanical Characteristics

- Package: DFN1006-2L (1.0X0.6X0.5mm)
- Lead Finish: Matte Tin
- Case Material: "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020

Applications

- Cellular Handsets and Accessories
- Display Ports
- MDDI Ports
- USB Ports
- Digital Visual Interface (DVI)
- PCI Express and Serial SATA Ports

Marking & Ordering information



* Remark : S is normal marking, if need special marking please contact with local tasund sales.

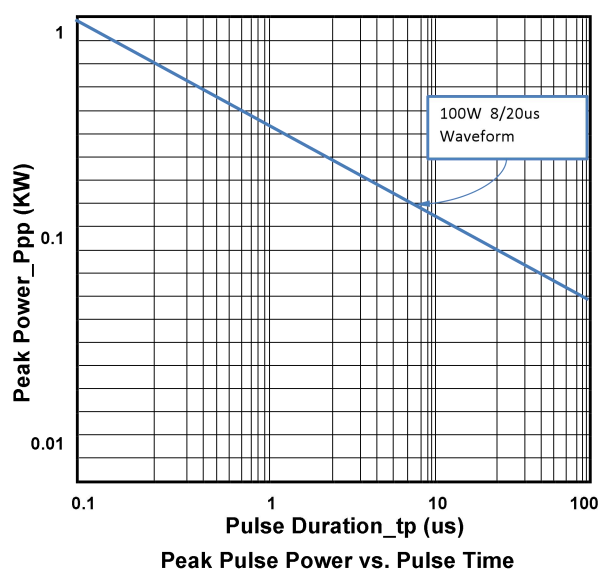
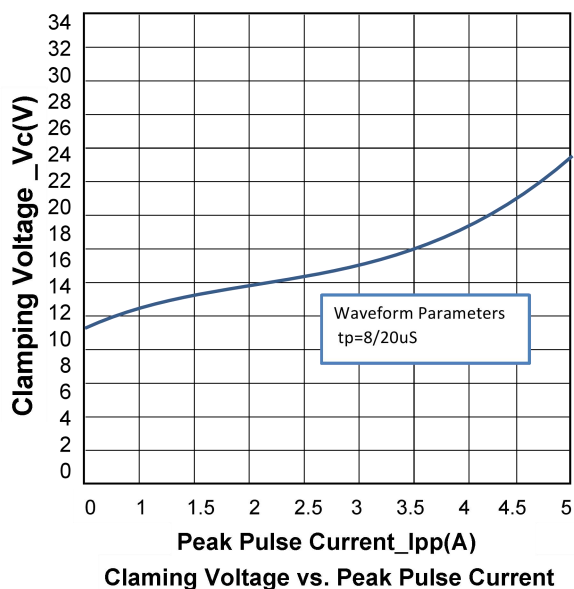
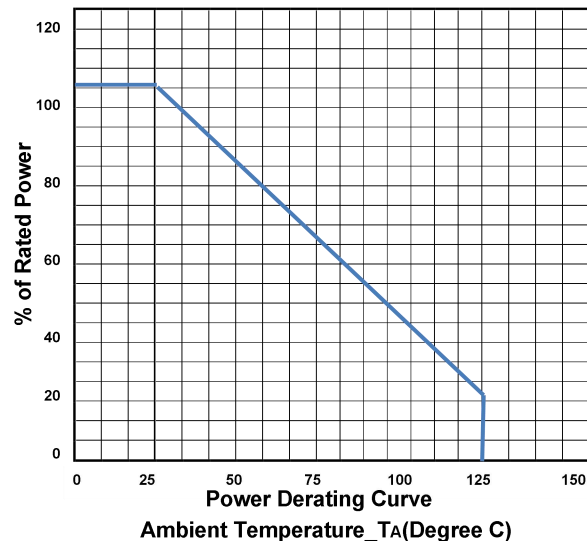
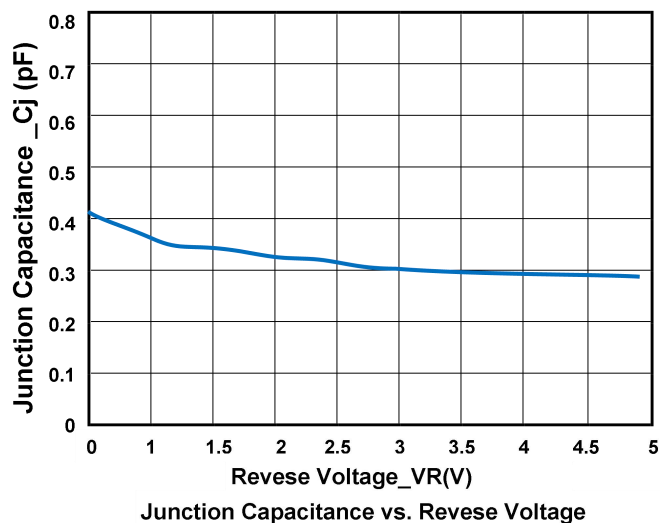
Absolute maximum ratings ($T_A=25^{\circ}\text{C}$, RH=45%-75%, unless otherwise noted)

Parameter	Symbol	Value	Unit
Peak Pulse Power ($t_p=8/20\mu\text{s}$ waveform)	P_{pp}	100	W
Peak Pulse Current (8/20 μs)	I_{pp}	4	A
ESD per IEC 61000-4-2 (Air)	V_{ESD}	± 20	kV
ESD per IEC 61000-4-2 (Contact)		± 15	
Operating Temperature Range	T_J	-55 to +125	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150	$^{\circ}\text{C}$

Electrical characteristics ($T_A=25^{\circ}\text{C}$)

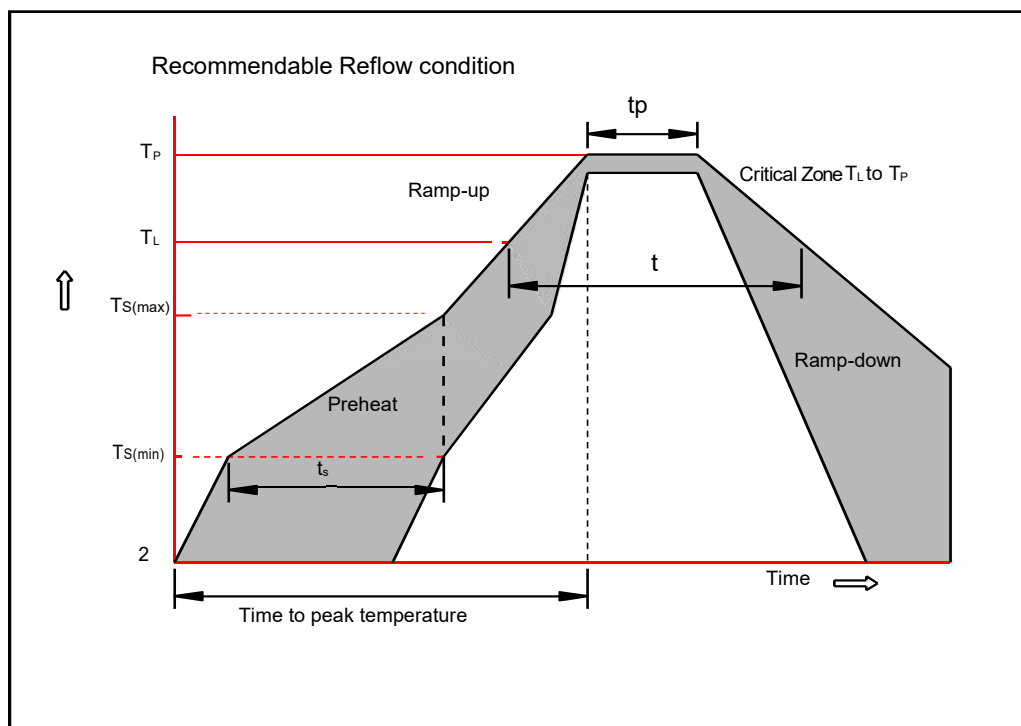
Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V_{RWM}			3.3	V	
Breakdown Voltage	V_{BR}	5			V	$I_T = 1\text{mA}$
Reverse Leakage Current	I_R			0.2	μA	$V_{RWM} = 3.3\text{ V}$
Clamping Voltage	V_C			11	V	$I_{PP} = 4\text{A}$ (8 x 20 μs pulse)
Clamping Voltage	V_C			25	V	$I_{PP} = 4\text{A}$ (8 x 20 μs pulse)
Junction Capacitance	C_J		0.25	0.3	pF	$V_R = 0\text{V}$, $f = 1\text{MHz}$

Typical Performance Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise Specified)

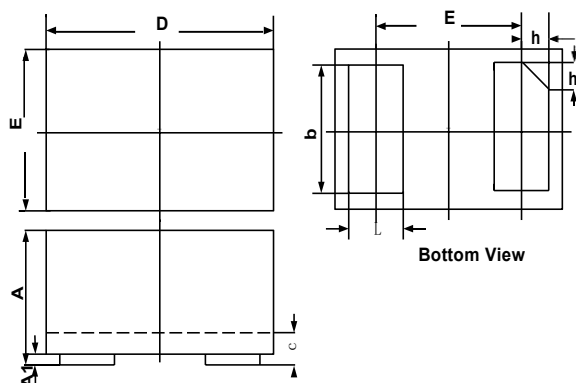


Soldering Parameter

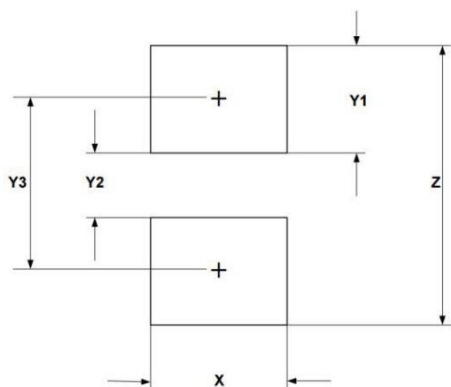
Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150°C
	-Temperature Max($T_{s(max)}$)	+200°C
	-Time (Min to Max) (t_s)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3°C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L) (Liquid us)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260°C



Package Mechanical Data



Suggested Land pattern of PCB design



SYM	DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.45	0.50	0.55	0.018	0.020	0.022
A1	0.00	0.02	0.05	0.000	0.001	0.002
b	0.45	0.50	0.55	0.018	0.020	0.022
c	0.12	0.15	0.18	0.005	0.006	0.007
D	0.95	1.00	1.05	0.037	0.039	0.041
e	0.65 BSC			0.026 BSC		
E	0.55	0.60	0.65	0.022	0.024	0.026
L	0.20	0.25	0.30	0.008	0.010	0.012
h	0.07	0.12	0.17	0.003	0.005	0.007

SYM	DIMENSIONS	
	MILLIMETERS	INCHES
X	0.60	0.024
Y1	0.50	0.020
Y2	0.30	0.012
Y3	0.80	0.032
Z	1.30	0.052